

### SOT-23-3 Pin Configuration

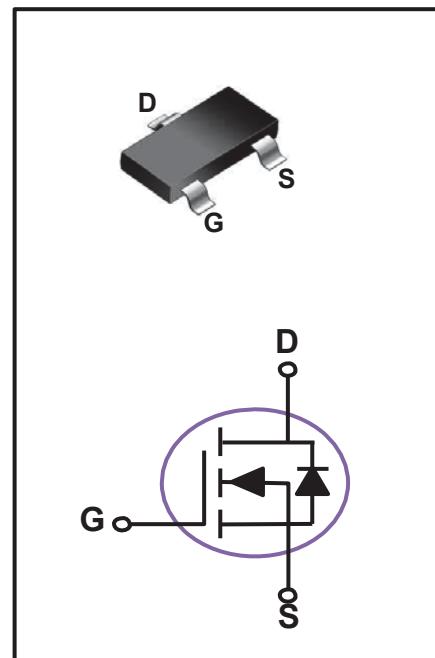
BVDSS	RDS <sub>ON</sub>	ID
60V	75mΩ	3.2A

#### Features

- 60V, 3.2A,  $RDS(ON) = 75m\Omega$  @  $VGS = 10V$
- Improved  $dv/dt$  capability
- Fast switching
- 100% EAS Guaranteed
- Green Device Available

#### Applications

- Motor Drive
- Power Tools
- LED Lighting



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current – Continuous ( $T_c=25^\circ C$ )	$I_D$	3.2	A
Drain Current – Continuous ( $T_c=100^\circ C$ )		2	A
Drain Current – Pulsed <sup>1</sup>	$I_{DM}$	12.8	A
Power Dissipation ( $T_c=25^\circ C$ )	$P_D$	1.56	W
Power Dissipation – Derate above 25°C		0.012	W/°C
Storage Temperature Range	$T_{STG}$	-50 to 150	°C
Operating Junction Temperature Range	$T_J$	-50 to 150	°C

#### Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to ambient	$R_{\theta JA}$	---	80	°C/W



# 60VN-ChannelMOSFETS

**LDN6912S**

**MOSFET ELECTRICAL CHARACTERISTICS**  $T_A=25^\circ\text{C}$  unless otherwise specified

## Off Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	60	---	---	V
$\text{BV}_{\text{DSS}}$ Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.05	---	$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{DS}}=60\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{\text{DS}}=48\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=125^\circ\text{C}$	---	---	10	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA

## On Characteristics

Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$ , $I_D=6\text{A}$	---	60	75	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$ , $I_D=3\text{A}$	---	70	90	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D = 250\mu\text{A}$	1.2	1.8	2.5	V
$V_{\text{GS}(\text{th})}$ Temperature Coefficient	$\Delta V_{\text{GS}(\text{th})}$		---	-5	---	$\text{mV}/^\circ\text{C}$
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=10\text{V}$ , $I_D=3\text{A}$	---	7	---	S

## Dynamic and switching Characteristics

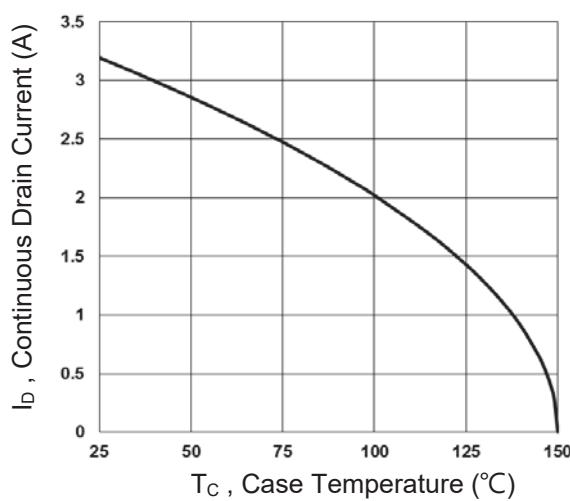
Total Gate Charge <sup>2, 3</sup>	$Q_g$	$V_{\text{DS}}=48\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $I_D=6\text{A}$	---	9.3	14	nC
Gate-Source Charge <sup>2, 3</sup>	$Q_{\text{gs}}$		---	2.1	4	
Gate-Drain Charge <sup>2, 3</sup>	$Q_{\text{gd}}$		---	1.8	4	
Turn-On Delay Time <sup>2, 3</sup>	$T_{\text{d(on)}}$	$V_{\text{DD}}=30\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=3.3\Omega$ $I_D=1\text{A}$	---	2.9	6	ns
Rise Time <sup>2, 3</sup>	$T_r$		---	9.5	18	
Turn-Off Delay Time <sup>2, 3</sup>	$T_{\text{d(off)}}$		---	18.4	35	
Fall Time <sup>2, 3</sup>	$T_f$		---	5.3	10	
Input Capacitance	$C_{\text{iss}}$		---	500	725	pF
Output Capacitance	$C_{\text{oss}}$	$V_{\text{DS}}=15\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $F=1\text{MHz}$	---	45	65	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	16	30	
Gate resistance	$R_g$	$V_{\text{GS}}=0\text{V}$ , $V_{\text{DS}}=0\text{V}$ , $F=1\text{MHz}$	---	2	4	$\Omega$

## Drain-Source Diode Characteristics and Maximum Ratings

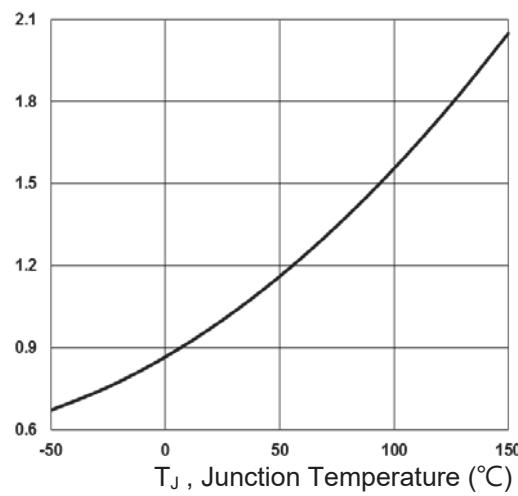
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	$I_s$	$V_G=V_D=0\text{V}$ , Force Current	---	---	3.2	A
Pulsed Source Current	$I_{\text{SM}}$		---	---	6.4	A
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}$ , $I_s=1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1	V
Reverse Recovery Time <sup>2</sup>	$t_{\text{rr}}$	$V_{\text{GS}}=30\text{V}$ , $I_s=1\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$	---	23.2	---	ns
Reverse Recovery Charge <sup>2</sup>	$Q_{\text{rr}}$	$T_J=25^\circ\text{C}$	---	14.3	---	nC

Note :

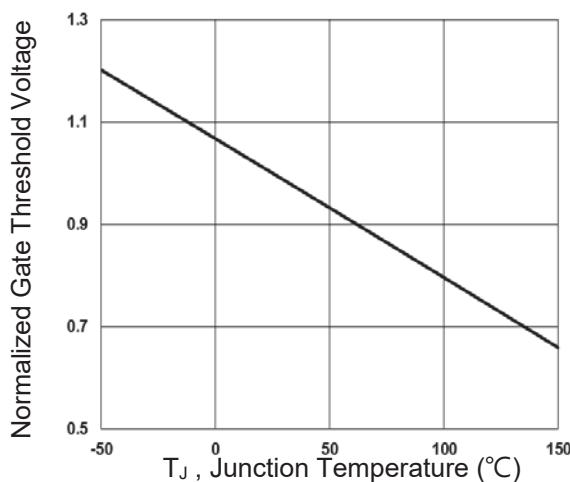
1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.



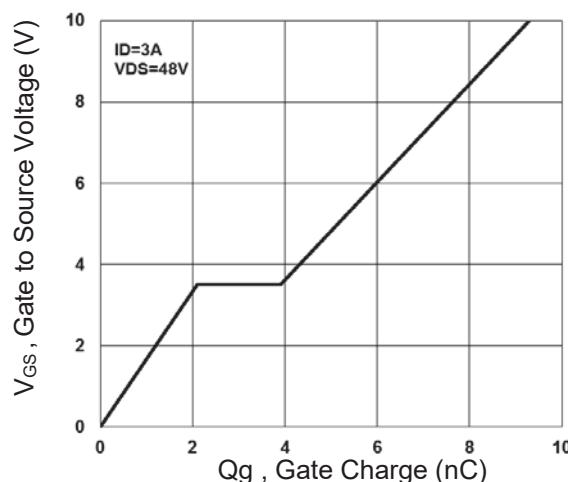
**Fig.1** Continuous Drain Current vs.  $T_c$



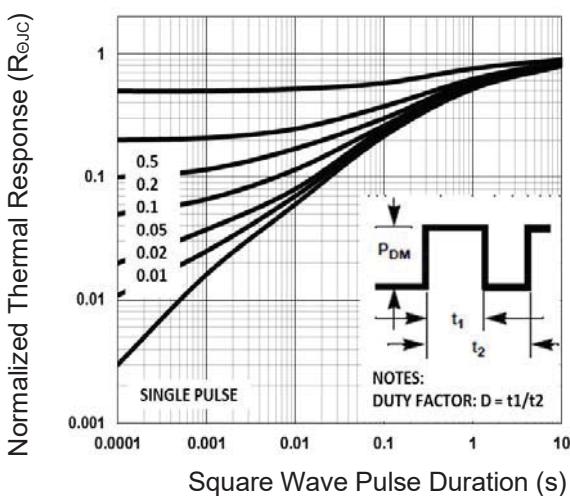
**Fig.2** Normalized RDSON vs.  $T_j$



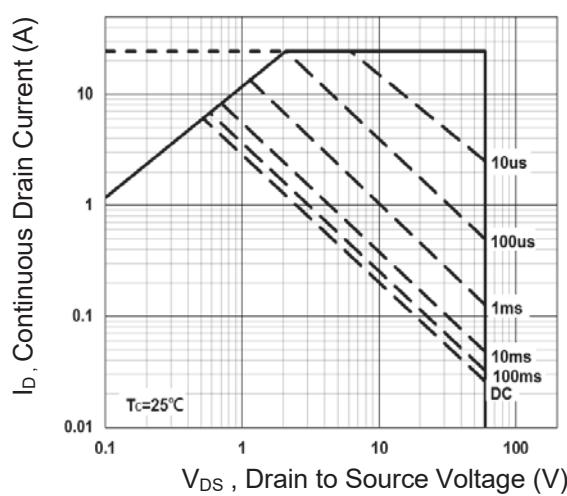
**Fig.3** Normalized  $V_{th}$  vs.  $T_j$



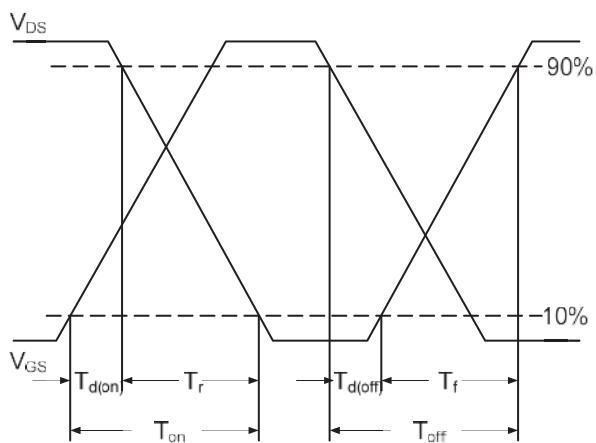
**Fig.4** Gate Charge Waveform



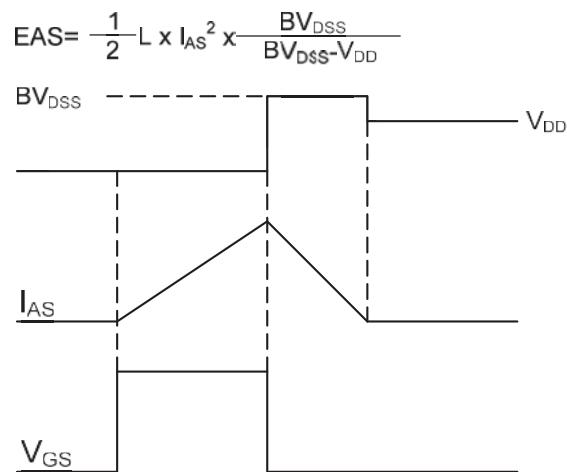
**Fig.5** Normalized Transient Response



**Fig.6** Maximum Safe Operation Area

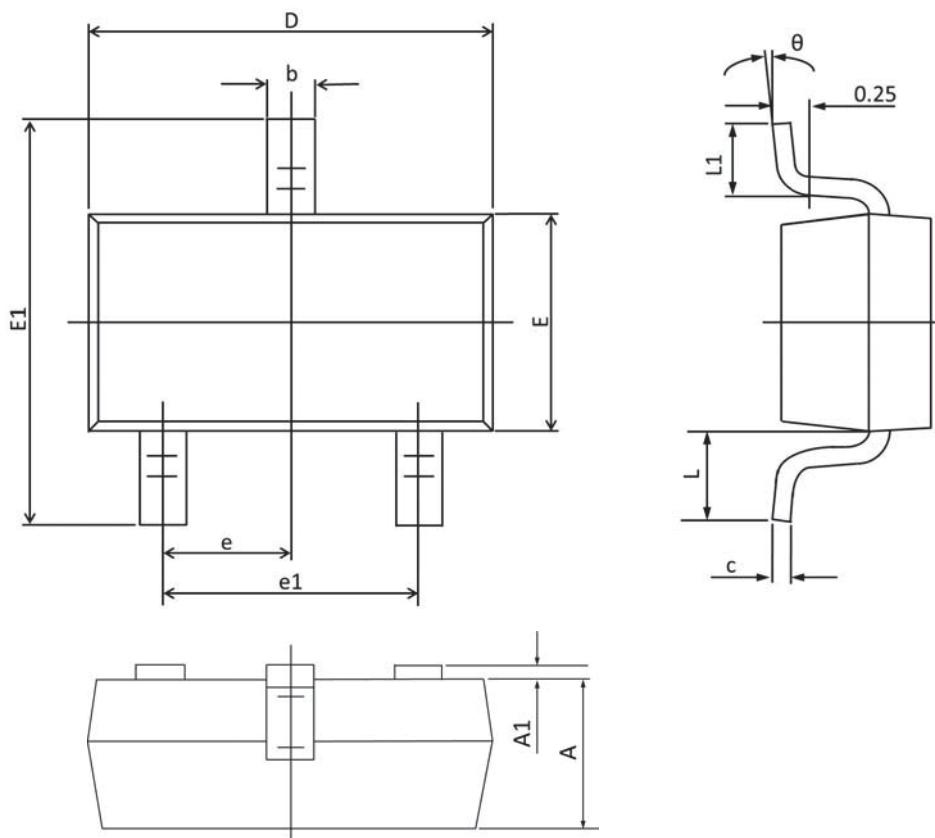


**Fig.7** Switching Time Waveform



**Fig.8** EAS Waveform

## SOT23-3S PACKAGE INFORMATION



Symbol	Dimensions In		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.000	0.03	0.039
A1	0.000	0.100	0.00	0.004
b	0.300	0.500	0.012	0.020
c	0.090	0.110	0.003	0.004
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
Θ	1°	7°	1°	7°